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		D.K.W. Lam, "Low temperature plasma chemical vapor deposition of silicon oxynitride thin-film waveguides", Applied Optics, Vol. 23, No. 16, August 15, 1984, pp. 2744-2746.						
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		A.J. Kenyon et al., "A luminescence study of silicon-rich silica and rare-earth doped silicon-rich silica", Electrochemical Society Proceedings Vol. 91-11, pp. 304-318.
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		G. Grand et al., "Low-Loss PECVD Silica Channel Waveguides for Optical Communications", Electronic Letters, Vol. 26, No. 25, December 6 1990, pp. 2135-21-37.					
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